

Abstract of the Disclosure

Source and drain diffusion layers by an extremely shallower box shaped highly doped impurity distribution that was not obtainable so far by the existent solid phase growing 5 is attained by liquid phase growing with no effects on the gate electrode thereby attaining low consumption power and operation at large current and higher speed in a micro-refined semiconductor device. Contact with inter-connection layer over the entire region of the source and drain diffusion layers 10 is enabled overstriding the gate electrode and without short circuit with the gate electrode by utilizing that the etching selectivity of an insulation film comprising Al as a main constituent atom is extremely higher with respect to an Si oxide film. Further, a metal film of a shallower decaying depth is 15 disposed selectively only to the contact region thereby selectively heating Si indirectly locally by a laser light having a wavelength with deep decaying depth to Si and, accordingly, less heating the Si itself to liquefy only the ion implanted amorphous region of the diffusion layer to enable formation 20 of source and drain junction in an extremely shallower box shaped highly doped impurity distribution.